

Vishay Semiconductors

COMPLIANT

HALOGEN

FREE

Hyperfast Rectifier, 8 A FRED Pt®



LINKS TO ADDITIONAL RESOURCES



| PRIMARY CHARACTERISTICS | | | | |
|----------------------------------|-------------------|--|--|--|
| I _{F(AV)} | 8 A | | | |
| V _R | 600 V | | | |
| V _F at I _F | 1.3 V | | | |
| t _{rr} (typ.) | 16 ns | | | |
| T _J max. | 175 °C | | | |
| Package | TO-220 FullPAK 2L | | | |
| Circuit configuration | Single | | | |

FEATURES

- · Hyperfast soft recovery time
- · Low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current
- Fully isolated package (V_{INS} = 2500 V_{RMS})
- True 2 pin package
- Designed and qualified according to JEDEC®-JESD 47
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

Hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

MECHANICAL DATA

Case: TO-220 FullPAK 2L

Molding compound meets UL 94 V-0 flammability rating

Terminals: matte tin plated leads, solderable per

J-STD-002

| ABSOLUTE MAXIMUM RATINGS | | | | |
|---|-----------------------------------|-------------------------|-------------|-------|
| PARAMETER | SYMBOL | TEST CONDITIONS | VALUES | UNITS |
| Peak repetitive reverse voltage | V _{RRM} | | 600 | V |
| Average rectified forward current in DC | I _{F(AV)} | T _C = 114 °C | 8 | |
| Non-repetitive peak surge current | I _{FSM} | T _J = 25 °C | 80 | A |
| Repetitive peak surge current Square wave 20 kHz duty cycle (50 %) | I _{FRM} | T _C = 96 °C | 16 | |
| Operating junction and storage temperatures | T _J , T _{Stg} | | -65 to +175 | °C |

| ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified) | | | | | | |
|--|-----------------|--|-----|------|-------|----|
| PARAMETER | SYMBOL | TEST CONDITIONS MIN. TYP. MAX. | | MAX. | UNITS | |
| Breakdown voltage, blocking voltage | V_{BR}, V_{R} | I _R = 100 μA | 600 | - | - | |
| Forward voltage | V _F | I _F = 8 A | - | 2.0 | 2.65 | V |
| Forward voltage V _F | ٧F | I _F = 8 A, T _J = 150 °C | - | 1.3 | 1.85 | |
| Poverse leakage ourrent | ı | $V_R = V_R$ rated | - | 0.02 | 12 | |
| Reverse leakage current | I _R | T _J = 150 °C, V _R = V _R rated | - | 15 | 100 | μA |
| Junction capacitance | C _T | V _R = 600 V - 6 - | | pF | | |
| Series inductance | L _S | Measured lead to lead 5 mm from package body - 8 - r | | nΗ | | |





www.vishay.com

Vishay Semiconductors

| DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified) | | | | | | | |
|---|--|--|---|------|------|------|-------|
| PARAMETER | SYMBOL | TEST CONDITIONS | | MIN. | TYP. | MAX. | UNITS |
| | | $I_F = 1 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$ | | - | 16 | 23 | |
| Reverse recovery time | | $I_F = 8 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$ | | - | 20 | 28 | |
| neverse recovery time | t _{rr} | T _J = 25 °C | | =. | 21 | - | ns |
| | | T _J = 125 °C | $I_F = 8 \text{ A},$ $dI_F/dt = 200 \text{ A/}\mu\text{s},$ $V_R = 390 \text{ V}$ | =. | 39 | - | |
| Peak recovery current | | T _J = 25 °C | | - | 3 | - | А |
| reak recovery current | I _{RRM} | T _J = 125 °C | | =. | 5 | - | ^ |
| Devenue receivem charge | 0 | T _J = 25 °C | | =. | 36 | - | nC |
| Reverse recovery charge | everse recovery charge Q _{rr} | T _J = 125 °C | | - | 108 | - | IIC |
| Reverse recovery time | t _{rr} | T _J = 125 °C | $I_F = 8 \text{ A},$ $dI_F/dt = 600 \text{ A/}\mu\text{s},$ $V_R = 390 \text{ V}$ | =. | 30 | - | ns |
| Peak recovery current | I _{RRM} | | | - | 13 | - | Α |
| Reverse recovery charge | Q _{rr} | | | - | 205 | - | nC |

| THERMAL - MECHANICAL SPECIFICATIONS | | | | | | |
|--|-----------------------------------|--|-----------|------|------------|------------------------|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNITS |
| Maximum junction and storage temperature range | T _J , T _{Stg} | | -65 | - | 175 | °C |
| Thermal resistance, junction-to-case | R _{thJC} | | - | 4.6 | 5.5 | |
| Thermal resistance, junction-to-ambient | R _{thJA} | Typical socket mount | - | - | 70 | °C/W |
| Typical thermal resistance, case-to-heatsink | R _{thCS} | Mounting surface, flat, smooth and greased | - | 0.5 | - | |
| Weight | | | - | 2 | - | g |
| vveignt | | | - | 0.07 | - | OZ. |
| Mounting torque | | | 6 (5) | - | 12 (10) | kgf · cm (lbf · in) |
| Marking device | | Case style TO-220 FullPAK 2L | ETH0806FP | | | |



Vishay Semiconductors

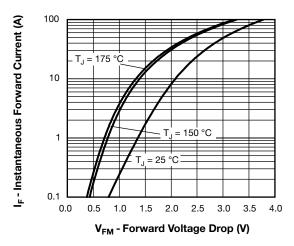


Fig. 1 - Typical Forward Voltage Drop Characteristics

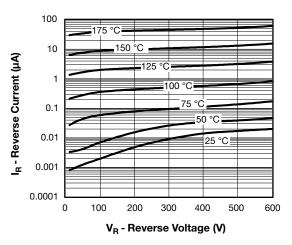


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

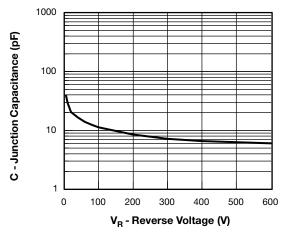


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

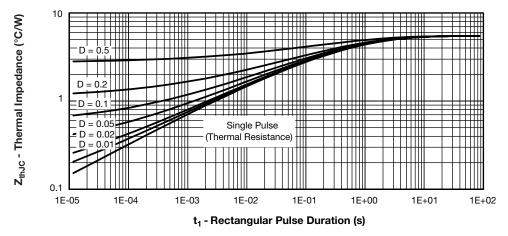


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

www.vishay.com

Vishay Semiconductors

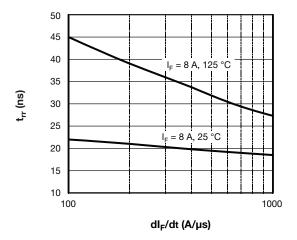


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

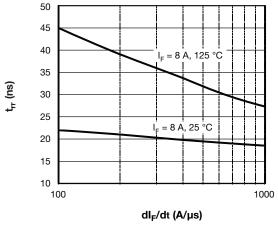


Fig. 7 - Typical Reverse Recovery vs. dI_F/dt

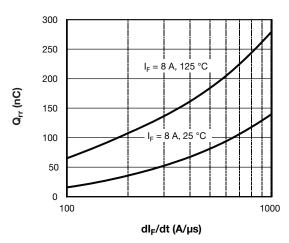


Fig. 6 - Forward Power Loss Characteristics

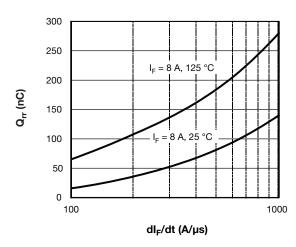
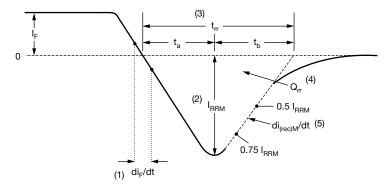


Fig. 8 - Typical Stored Charge vs. dl_F/dt



- (1) di_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RBM} and 0.50 I_{RBM} extrapolated to zero current.
- (4) $\mathbf{Q}_{\rm rr}$ area under curve defined by $\mathbf{t}_{\rm rr}$ and $\mathbf{I}_{\rm RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $di_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

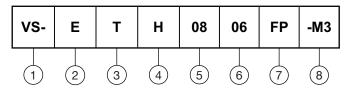
Fig. 9 - Reverse Recovery Waveform and Definitions



Vishay Semiconductors

ORDERING INFORMATION TABLE

Device code



Vishay Semiconductors product

2 - Circuit configuration:

E = single

3 - T = TO-220

4 - H = hyperfast recovery time

5 - Current code: 08 = 8 A

6 - Voltage code: 06 = 600 V

7 - FP = TO-220 FullPAK 2L

8 - Environmental digit:

-M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

| ORDERING INFORMATION (Example) | | | | | | |
|--------------------------------|---|------|-------------------------|--|--|--|
| PREFERRED P/N | RRED P/N QUANTITY PER TUBE MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION | | | | | |
| VS-ETH0806FP-M3 | 50 | 1000 | Antistatic plastic tube | | | |

| LINKS TO RELATED DOCUMENTS | | | | |
|----------------------------|--------------------------|--|--|--|
| Dimensions | www.vishay.com/doc?96157 | | | |
| Part marking information | www.vishay.com/doc?95392 | | | |
| SPICE model | www.vishay.com/doc?96865 | | | |



Legal Disclaimer Notice

Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.